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Review

Silicon nanowires as field-effect transducers for biosensor development: A review



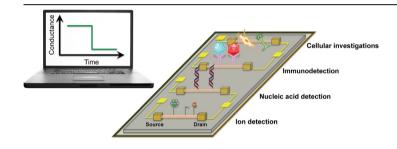
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HIGHLIGHTS

- Nanoscale field-effect transducers interrogate surface charge by conductivity changes.
- The nanometer dimensions of SiNWs facilitate sensitive detection of biomolecules.
- SiNWs can be fabricated by bottom up or top–down approaches.
- Device parameters and solutionphase conditions strongly influence analytical performance.

GRAPHICAL ABSTRACT



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ABSTRACT

The unique electronic properties and miniaturized dimensions of silicon nanowires (SiNWs) are attractive for label-free, real-time and sensitive detection of biomolecules. Sensors based on SiNWs operate as field effect transistors (FETs) and can be fabricated either by top-down or bottom-up approaches. Advances in fabrication methods have allowed for the control of physicochemical and electronic properties of SiNWs, providing opportunity for interfacing of SiNW-FET probes with intracellular environments. The Debye screening length is an important consideration that determines the performance and detection limits of SiNW-FET sensors, especially at physiologically relevant conditions of ionic strength (>100 mM). In this review, we discuss the construction and application of SiNW-FET sensors for detection of ions, nucleic acids and protein markers. Advantages and disadvantages of the top-down and bottom-up approaches for synthesis of SiNWs are discussed. An overview of various

Abbreviations: 1 BPM, 1 base pair mismatch; 1-D, 1-dimensional; 2-MEA, 2-mercaptoethylamine; 3-D, 3-dimensional; Act-D, actinomycin-D; Ad, adamantane; AIV, avian influenza virus; AMPs, antibody mimic proteins; anti-cTnl, antibody for cTnl; anti-hlgG, antibody for human IgG; APTES, 3-aminopropyltriethoxysilane; ASIC, application specific integrated circuit; β-CD, β-cyclodextrin; BB, blown-bubble; BG, back-gate; BIT-FET, branched intracellular nanotube FET; BP, base pair; BSA, bovine serum albumin; CaM, calmodulin; CEA, carcinoembryonic antigen; CK-MB, creatine kinase MB; CK-MM, creatine kinase MM; CMOS, complementary metal oxide semiconductor; cTnl, cardiac Troponin I; cTnT, cardiac Troponin T; CVD, chemical vapor deposition; D, drain; DG, double-gate; DMPC, 1,2-dimyristoyl-sn-glycero-3-phosphocholine; DNA, deoxyribonucleic acid; DTT, dithiothreitol; ECG, electrocardiogram; EDTA, ethylenediaminotetraacetic acid; ELISA, enzyme-linked immunosorbent assay; FC, fully-complementary; FET, Field effect transistor; FG, front-gate; G, gate; GSH, glutathione; GST, glutathione S-transferase; H-terminated, hydrogen terminated; hlgG, human IgG; His-tag, histidine tag; I_{sd} , source-drain current; LB, Langmuir-Blodgett; LOD, limit of detection; mAb, monoclonal antibody; mES, mouse embryonic stem; MPTES, 3-mercaptopropyltriethoxysilane; MPTMS, 3-mercaptopropyltrimethoxysilane; NC, non-complementary; NTA, nitrilotriacetic acid; NW, nanowire; PBS, phosphate buffered saline; PDMS, polydimethylsiloxane; PNA, peptide nucleic acid; PSA, prostate specific antigen; PSAα1, PSA-α1-antichymotrypsin; RCA, rolling circle amplification; RE, reference electrode; S, source; SEM, scanning electron microscope; SiNW, Silicon nanowire; siRNA, small interfering RNA; SNP, single nucleotide polymorphism; SOI, siliconon-insulator; SSC, saline sodium citrate; ssDNA, single-stranded DNA; TCEP, tris(2-carboxyethyl) phosphine; TEM, transmission electron microscope; TNF-α, tumor necrosis factor-alpha; TUNEL, terminal deoxynucleotidyl transferase dU

* Corresponding author. Tel. +1 905 828 5437; fax: +1 905 828 5425. E-mail address: ulrich.krull@utoronto.ca (U. J. Krull). Gating Debye length methods for surface functionalization of SiNWs for immobilization of selective chemistry is provided in the context of impact on the analytical performance of SiNW-FET sensors. In addition to *in vitro* examples, an overview of the progress of use of SiNW-FET sensors for *ex vivo* studies is also presented. This review concludes with a discussion of the future prospects of SiNW-FET sensors.

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1. Introduction

The integration of nanomaterials into device structures for biosensing applications has played a central role in the development of new strategies for signal transduction [1,2]. Due to comparable sizes of biological macromolecules and nanomaterials (nanotubes, nanowires and nanoparticles), the combination of nanomaterials with biomolecules offers potential for development of sensing technologies of molecular size scale for sensitive detection of biomolecules [2]. Silicon nanowires (SiNWs) are a class of 1-dimensional (1-D) nanomaterial that was introduced in 2001 by the Lieber group [3]. Since this time SiNWs have been described in numerous studies as electrical field-based sensors that are suitable for a variety of applications that include detection of ions [4,5], small molecules [6,7], nucleic acids [8], proteins [9] and the investigation of the electrophysiology

associated with single cells [10-13] and tissues [14,15]. SiNWs can be synthesized as single crystals, and owing to their 1-D morphology and resulting increase in surface area-to-volume ratio, they provide improved analytical sensitivity as compared to planar field effect transistor (FET) devices for chemical and biosensing [16,17]. Advances in synthetic approaches for fabrication of SiNWs have allowed for the control of morphology and doping levels of SiNWs [18], enabling SiNW-FETs for cellular studies with high spatial and temporal resolution [19]. Additionally, SiNWs offer label-free, real-time and ultrasensitive detection of biomolecules to sub-fM detection limits [20]. These detection limits are 2-3 orders of magnitude lower than those that have been reported with quantum dots and carbon nanotubes for ensemble compatible measurements [1]. Top-down fabrication of sensors based on silicon nanostructures offers the practical advantage of compatibility with the established fabrication

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